

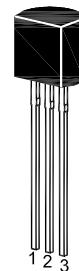
2SC1623

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups, O, Y, G and L, according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.



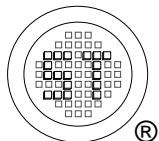
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 6 \text{ V}$, $I_C = 1 \text{ mA}$	h_{FE}	90	-	180	-
	h_{FE}	135	-	270	-
	h_{FE}	200	-	400	-
	h_{FE}	300	-	600	-
Collector Base Cutoff Current at $V_{CB} = 60 \text{ V}$	I_{CBO}	-	-	0.1	μA
Emitter Base Cutoff Current at $V_{EB} = 5 \text{ V}$	I_{EBO}	-	-	0.1	μA
Collector Base Breakdown Voltage at $I_C = 100 \mu\text{A}$	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 10 \text{ mA}$	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10 \mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $I_C = 100 \text{ mA}$, $I_B = 10 \text{ mA}$	$V_{CE(sat)}$	-	0.15	0.3	V
Base Emitter Saturation Voltage at $I_C = 100 \text{ mA}$, $I_B = 10 \text{ mA}$	$V_{BE(sat)}$	-	0.86	1	V
Gain Bandwidth Product at $V_{CE} = 6 \text{ V}$, $I_C = 10 \text{ mA}$	f_T	-	250	-	MHz
Output Capacitance at $V_{CB} = 6 \text{ V}$, $f = 1 \text{ MHz}$	C_{ob}	-	3	-	pF



SEMTECH ELECTRONICS LTD.



ISO/TS 16949 : 2009
Certificate No. 1071300



ISO14001 : 2004
Certificate No. 7116



ISO 9001 : 2008
Certificate No. 50713410



BS-OHSAS 18001 : 2007
Certificate No. 7116



IECO OC 080000
Certificate No. PRC-HSPM-1031